



[Web](#) [Images](#) [Groups](#) [News](#) [Froogle](#) [Local](#)^{New!} [more »](#)
 [Advanced Search](#) [Preferences](#)

The "AND" operator is unnecessary -- we include all search terms by default. [\[details\]](#)

Web

Results 1 - 10 of about 32 for "**field shield**" and "JFET". (0.42 seconds)

Hagerman Technology LLC: Trumpet Phono

The sheet metal chassis forms a complete electric **field shield** around the ...
 Now available with built-in differential JFET headamp for 66dB of moving coil ...
www.hagtech.com/trumpet.html - 24k - [Cached](#) - [Similar pages](#)

US Patent Class 257-- ACTIVE SOLID-STATE DEVICES (EG, TRANSISTORS ...

... with channel much wider than length between source and drain (eg, power JFET)
 ... With means to increase breakdown voltage (eg, **field shield** electrode, ...
www.patentec.com/data/class/257.html - 142k - [Cached](#) - [Similar pages](#)

PTO Manual of Classification for US patents

... channel much wider than length between source and drain (eg, power JFET) 288 .
 ... With means to increase breakdown voltage (eg, **field shield** electrode, ...
www.ibiblio.org/patents/class/CLASS257.html - 67k - [Cached](#) - [Similar pages](#)

Class Schedule for Class 257 ACTIVE SOLID-STATE DEVICES (EG ...

... channel much wider than length between source and drain (eg, power JFET) ...
 to increase breakdown voltage (eg, **field shield** electrode, guard ring, etc. ...
www.uspto.gov/go/classification/uspc257/sched257.htm - 513k - [Cached](#) - [Similar pages](#)

Class Definition for Class 257 - ACTIVE SOLID-STATE DEVICES (EG ...

256., and 257, for light responsive PIN device combined with JFET. 257., and 258,
 for JFET. ... 340., 394, and 630, for **field shield** electrode. ...
www.uspto.gov/go/classification/uspc257/defs257.htm - 513k - [Cached](#) - [Similar pages](#)

[PDF] High-resolution, energy-dispersive microcalorimeter spectrometer ...

File Format: PDF/Adobe Acrobat - [View as HTML](#)
 using a silicon junction field effect transistor (JFET) operated ... superconducting
 magnet, magnetic **field shield** (made of. vanadium permendur, an Fe-Co-V ...
museum.nist.gov/exhibits/timeline/pdf/microcalorimeter.pdf - [Similar pages](#)

Performance lateral double-diffused MOS transistor - US Patent ...

... The addition of an enhanced-dopant concentration JFET gate region allows the ...
 257/409With means to increase breakdown voltage (eg, **field shield** electrode, guard ...
www.patentstorm.us/patents/5304827.html - 34k - Supplemental Result - [Cached](#) - [Similar pages](#)

Active solid-state devices (eg, transistors, solid-state diodes ...

409 · With means to increase breakdown voltage (eg, **field shield** electrode, ...
 E27.148 · Junction field effect transistor (JFET) imager or static induction ...
[www.patentstorm.us/class/257-Active_solid_state_devices_\(e_g,_transistors,_solid_state_diodes\).html](http://www.patentstorm.us/class/257-Active_solid_state_devices_(e_g,_transistors,_solid_state_diodes).html) - 513k - [Cached](#) - [Similar pages](#)
 [More results from www.patentstorm.us]

US Patent Subclass 257/213 - FIELD EFFECT DEVICE

409 with means to increase breakdown voltage (eg, **field shield** electrode, guard
 ring, etc.) - 410 gate insulator includes material (including air or ...
expaterra.com/usclassC257S213000m.html - 71k - Supplemental Result - [Cached](#) - [Similar pages](#)

[\[PDF\]](#) [The Quasi-Punch-Through Structure for Power Semiconductor Devices](#)

File Format: PDF/Adobe Acrobat - [View as HTML](#)

QPT Structure, closely located deep trenches are used to act as an electric **field shield** like The N buffer in. The PT IGBTs. Similar approaches was used in ...

www.ece.rutgers.edu/~ksheng/research/pdf/ipemc00_qpt.pdf - Supplemental Result - [Similar pages](#)

Google ►

Result Page: [1](#) [2](#) [3](#) [Next](#)



Free! Instantly find your email, files, media and web history. [Download now.](#)

[Search within results](#) | [Language Tools](#) | [Search Tips](#) | [Dissatisfied? Help us improve](#)

[Google Home](#) - [Advertising Programs](#) - [Business Solutions](#) - [About Google](#)

©2005 Google

Refine Search

Search Results -

Terms	Documents
5216275	154

Database:	<input checked="" type="checkbox"/> US Pre-Grant Publication Full-Text Database <input checked="" type="checkbox"/> US Patents Full-Text Database <input type="checkbox"/> US OCR Full-Text Database <input type="checkbox"/> EPO Abstracts Database <input type="checkbox"/> JPO Abstracts Database <input type="checkbox"/> Derwent World Patents Index <input type="checkbox"/> IBM Technical Disclosure Bulletins
------------------	---

Search:	<input type="text" value="L16"/>	<input type="button" value="Up"/>	<input type="button" value="Down"/>	<input type="button" value="Refine Search"/>
		<input type="button" value="Recall Text"/>	<input type="button" value="Clear"/>	<input type="button" value="Interrupt"/>

Search History

DATE: Friday, November 04, 2005 [Printable Copy](#) [Create Case](#)

<u>Set Name</u> <u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
side by side		result set
· <i>DB=USPT; PLUR=YES; OP=OR</i>		
<u>L16</u> 5216275	154	<u>L16</u>
<u>L15</u> 5168331	59	<u>L15</u>
· <i>DB=PGPB; PLUR=YES; OP=OR</i>		
<u>L14</u> L13 and JFET	0	<u>L14</u>
<u>L13</u> 20040084721	1	<u>L13</u>
<u>L12</u> 20040084721 A1	1006204	<u>L12</u>
· <i>DB=PGPB,EPAB; PLUR=YES; OP=OR</i>		
<u>L11</u> EP 1073110	2427939	<u>L11</u>
· <i>DB=EPAB; PLUR=YES; OP=OR</i>		
<u>L10</u> EP 1073110 A1	2339121	<u>L10</u>
· <i>DB=PGPB,EPAB; PLUR=YES; OP=OR</i>		
<u>L9</u> EP 1073110 A1	3345430	<u>L9</u>
· <i>DB=EPAB; PLUR=YES; OP=OR</i>		
<u>L8</u> ep 1073110 a1	2339121	<u>L8</u>

DB=PGPB; PLUR=YES; OP=OR

L7 JFET and "field shield" 2 L7

DB=USPT; PLUR=YES; OP=OR

L6 JFET and "field shield" 2 L6

DB=PGPB; PLUR=YES; OP=OR

L5 L3 and substrate 1 L5

L4 L3 asnd substrate 253022 L4

L3 L2 1 L3

L2 L1 and "shield electrode" 1 L2

L1 20050167695 1 L1

END OF SEARCH HISTORY

Refine Search

Search Results -

Terms	Documents
20050167695 and "field shield"	1

Database: US Pre-Grant Publication Full-Text Database
 US Patents Full-Text Database
 US OCR Full-Text Database
 EPO Abstracts Database
 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search: L18 **Refine Search**

Recall Text  **Clear** **Interrupt**

Search History

DATE: Friday, November 04, 2005 [Printable Copy](#) [Create Case](#)

Set Name Query
 side by side

Hit Count Set Name
 result set

DB=PGPB; PLUR=YES; OP=OR

<u>L18</u>	20050167695 and "field shield"	1	<u>L18</u>
<u>L17</u>	L13	1	<u>L17</u>

DB=USPT; PLUR=YES; OP=OR

<u>L16</u>	5216275	154	<u>L16</u>
<u>L15</u>	5168331	59	<u>L15</u>

DB=PGPB; PLUR=YES; OP=OR

<u>L14</u>	L13 and JFET	0	<u>L14</u>
<u>L13</u>	20040084721	1	<u>L13</u>

<u>L12</u>	20040084721 A1	1006204	<u>L12</u>
------------	----------------	---------	------------

DB=PGPB,EPAB; PLUR=YES; OP=OR

<u>L11</u>	EP 1073110	2427939	<u>L11</u>
------------	------------	---------	------------

DB=EPAB; PLUR=YES; OP=OR

<u>L10</u>	EP 1073110 A1	2339121	<u>L10</u>
------------	---------------	---------	------------

DB=PGPB,EPAB; PLUR=YES; OP=OR

<u>L9</u>	EP 1073110 A1	3345430	<u>L9</u>
<i>DB=EPAB; PLUR=YES; OP=OR</i>			
<u>L8</u>	ep 1073110 a1	2339121	<u>L8</u>
<i>DB=PGPB; PLUR=YES; OP=OR</i>			
<u>L7</u>	JFET and "field shield"	2	<u>L7</u>
<i>DB=USPT; PLUR=YES; OP=OR</i>			
<u>L6</u>	JFET and "field shield"	2	<u>L6</u>
<i>DB=PGPB; PLUR=YES; OP=OR</i>			
<u>L5</u>	L3 and substrate	1	<u>L5</u>
<u>L4</u>	L3 asnd substrate	253022	<u>L4</u>
<u>L3</u>	L2	1	<u>L3</u>
<u>L2</u>	L1 and "shield electrode"	1	<u>L2</u>
<u>L1</u>	20050167695	1	<u>L1</u>

END OF SEARCH HISTORY



Web Images Groups News Froogle Local^{New!} [more »](#)

[Advanced Search](#)
[Preferences](#)

The "AND" operator is unnecessary -- we include all search terms by default. [\[details\]](#)

Web

Results 1 - 10 of about 32 for "field shield" and "JFET". (0.42 seconds)

Hagerman Technology LLC: Trumpet Phono

The sheet metal chassis forms a complete electric **field shield** around the ...
 Now available with built-in differential **JFET** headamp for 66dB of moving coil ...
www.hagtech.com/trumpet.html - 24k - [Cached](#) - [Similar pages](#)

US Patent Class 257-- ACTIVE SOLID-STATE DEVICES (EG, TRANSISTORS ...

... with channel much wider than length between source and drain (eg, power **JFET**)
 ... With means to increase breakdown voltage (eg, **field shield** electrode, ...
www.patentec.com/data/class/257.html - 142k - [Cached](#) - [Similar pages](#)

PTO Manual of Classification for US patents

... channel much wider than length between source and drain (eg, power **JFET**) 288 .
 ... With means to increase breakdown voltage (eg, **field shield** electrode, ...
www.ibiblio.org/patents/class/CLASS257.html - 67k - [Cached](#) - [Similar pages](#)

Class Schedule for Class 257 ACTIVE SOLID-STATE DEVICES (EG ...

... channel much wider than length between source and drain (eg, power **JFET**) ...
 to increase breakdown voltage (eg, **field shield** electrode, guard ring, etc. ...
www.uspto.gov/go/classification/uspc257/sched257.htm - 513k - [Cached](#) - [Similar pages](#)

Class Definition for Class 257 - ACTIVE SOLID-STATE DEVICES (EG ...

256,, and 257, for light responsive PIN device combined with **JFET**. 257,, and 258,
 for **JFET**. ... 340,, 394, and 630, for **field shield** electrode. ...
www.uspto.gov/go/classification/uspc257/defs257.htm - 513k - [Cached](#) - [Similar pages](#)

[PDF] High-resolution, energy-dispersive microcalorimeter spectrometer ...

File Format: PDF/Adobe Acrobat - [View as HTML](#)
 using a silicon junction field effect transistor (**JFET**) operated ... superconducting
 magnet, magnetic **field shield** (made of. vanadium permendur, an Fe-Co-V ...
museum.nist.gov/exhibits/timeline/pdf/microcalorimeter.pdf - [Similar pages](#)

Performance lateral double-diffused MOS transistor - US Patent ...

... The addition of an enhanced-dopant concentration **JFET** gate region allows the ...
 257/409With means to increase breakdown voltage (eg, **field shield** electrode, guard ...
www.patentstorm.us/patents/5304827.html - 34k - [Supplemental Result](#) - [Cached](#) - [Similar pages](#)

Active solid-state devices (eg, transistors, solid-state diodes ...

409 · With means to increase breakdown voltage (eg, **field shield** electrode, ...
 E27.148 · Junction field effect transistor (**JFET**) imager or static induction ...
[www.patentstorm.us/class/257-Active_solid_state_devices_\(e.g._transistors,_solid_state_diodes\).html](http://www.patentstorm.us/class/257-Active_solid_state_devices_(e.g._transistors,_solid_state_diodes).html) - 513k - [Cached](#) - [Similar pages](#)
 [[More results from www.patentstorm.us](#)]

US Patent Subclass 257/213 - FIELD EFFECT DEVICE

409 with means to increase breakdown voltage (eg, **field shield** electrode, guard
 ring, etc.) - 410 gate insulator includes material (including air or ...
expaterra.com/usclassC257S213000m.html - 71k - [Supplemental Result](#) - [Cached](#) - [Similar pages](#)

[PDF] [The Quasi-Punch-Through Structure for Power Semiconductor Devices](#)

File Format: PDF/Adobe Acrobat - [View as HTML](#)

QPT Structure, closely located deep trenches are used to act as an electric **field shield** like The N buffer in. The PT IGBTs. Similar approaches was used in ...

www.ece.rutgers.edu/~ksheng/research/pdf/ipemc00_qpt.pdf - Supplemental Result - [Similar pages](#)

Google ►

Result Page: 1 2 3 [Next](#)



Google Desktop Search

9:30 AM

Free! Instantly find your email, files, media and web history. [Download now.](#)

[Search within results](#) | [Language Tools](#) | [Search Tips](#) | [Dissatisfied? Help us improve](#)

[Google Home](#) - [Advertising Programs](#) - [Business Solutions](#) - [About Google](#)

©2005 Google